MICROWAVE POWER GaAs FET TIM1213-8UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET ·HIGH POWER
- P1dB= 39.0dBm at 12.7GHz to 13.2GHz

•HIGH GAIN G1dB= 8.0dB at 12.7GHz to 13.2GHz

• LOW INTERMODULATION DISTORTION IM3= -45dBc at Pout= 27.0dBm Single Carrier Level

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 2.0A f = 12.7 to 13.2GHz	dBm	38.5	39.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.0	8.0	
Drain Current	IDS1		А	_	2.0	2.5
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%		33	
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 27.0dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-42	-45	
Drain Current	IDS2		А		2.0	2.5
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C			80

Recommended Gate Resistance(Rg): 100 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 2.4A	S	_	2.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 72mA	V	-0.5	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А		4.0	
Gate-Source Breakdown Voltage	VGSO	IGS= -72µA	V	-5		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		3.0	3.7

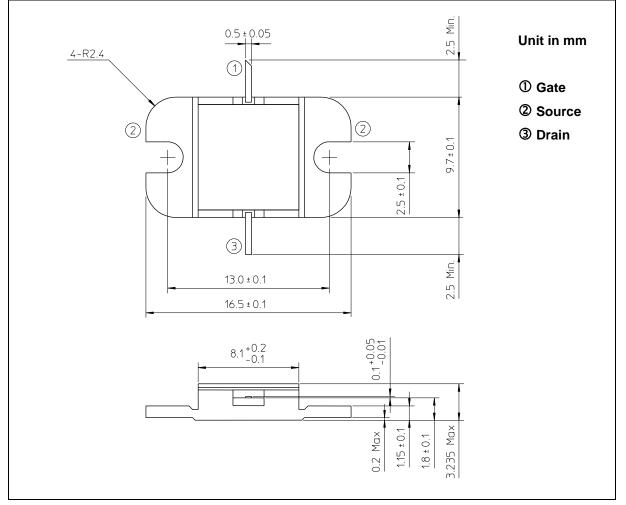
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	5.7
Total Power Dissipation (Tc= 25°C)	PT	W	40.5
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-9D1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

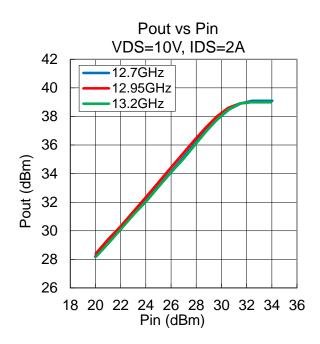
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

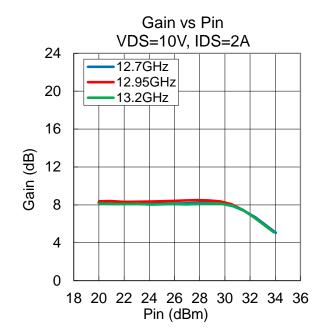
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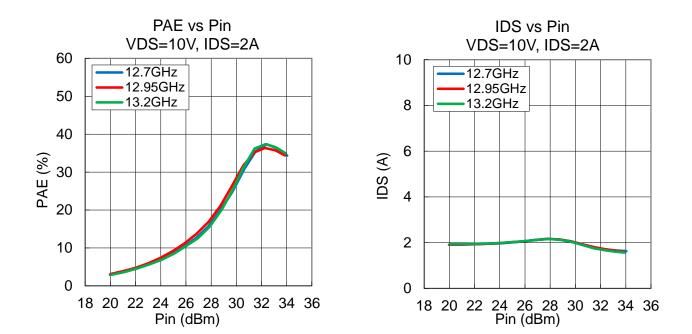
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 2.0 A, f= 12.7, 12.95, 13.2 GHz, Ta= +25 °C







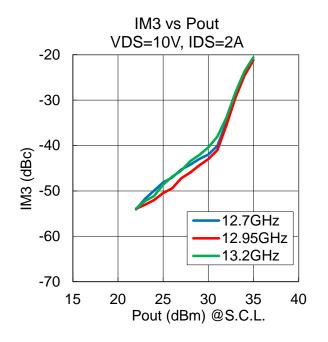
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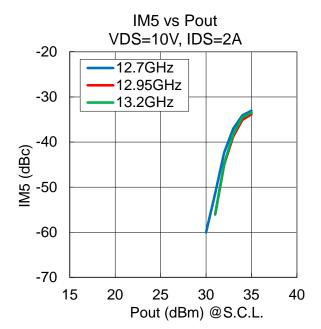
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 2.0 A, f= 12.7, 12.95, 13.2 GHz, Δf= 5 MHz , Ta= +25 °C



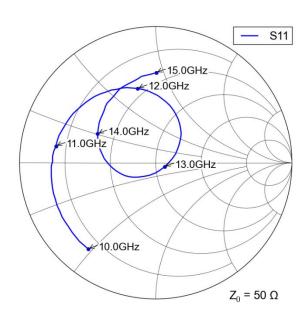


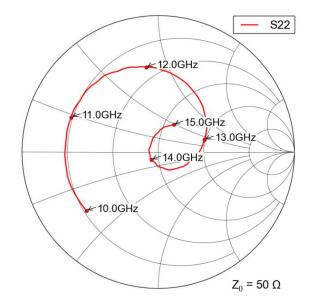
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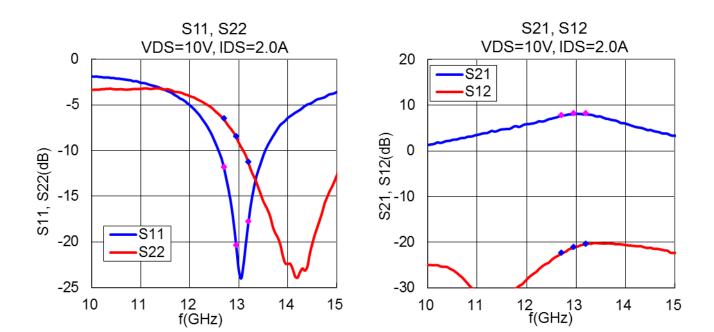
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 10 V, IDSset= 2.0 A, f= 10.0 to 15.0 GHz, Ta= +25 °C







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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